Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	50MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LVD, PWM, WDT
Number of I/O	70
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08qe128clk

Table of Contents

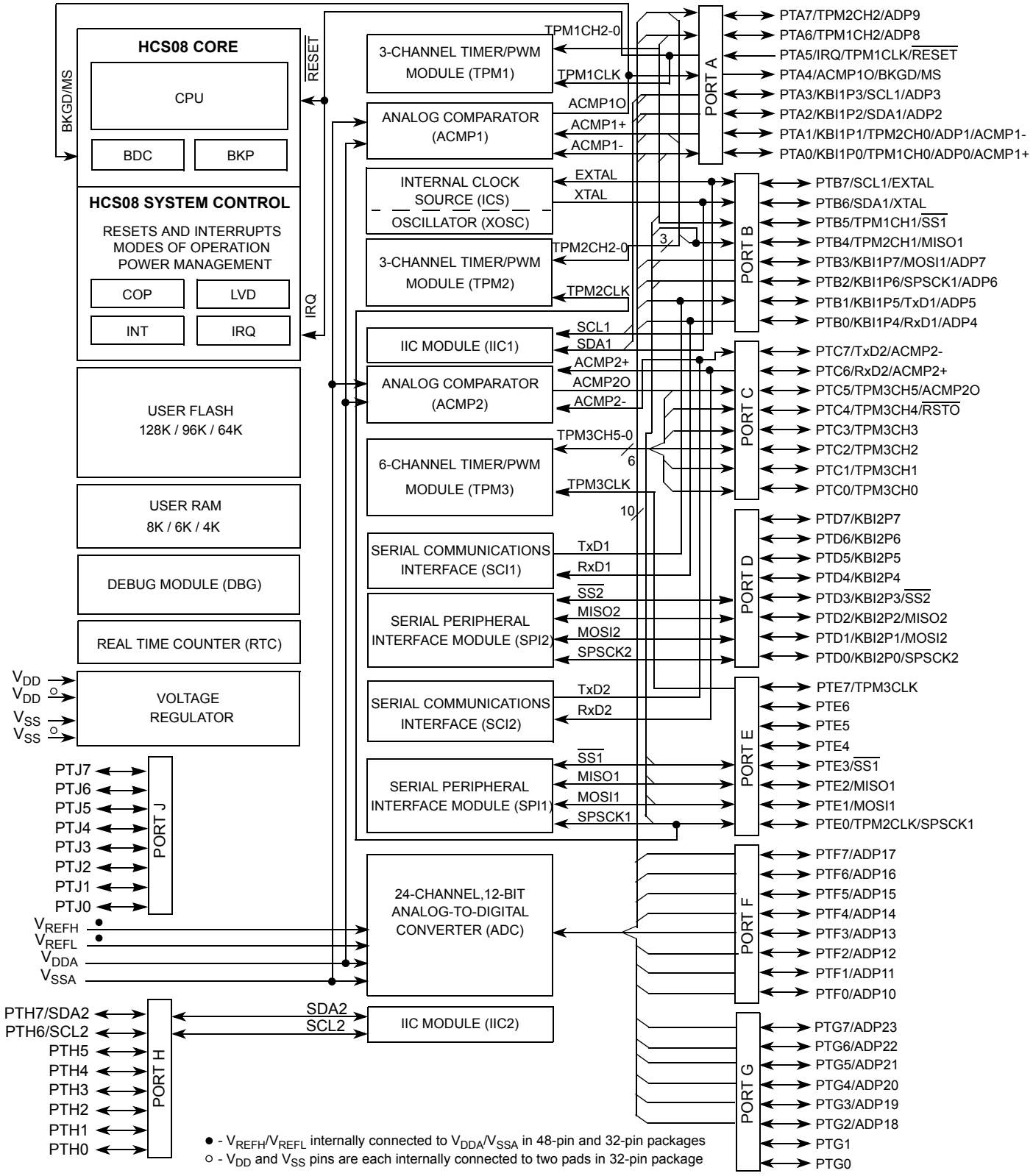
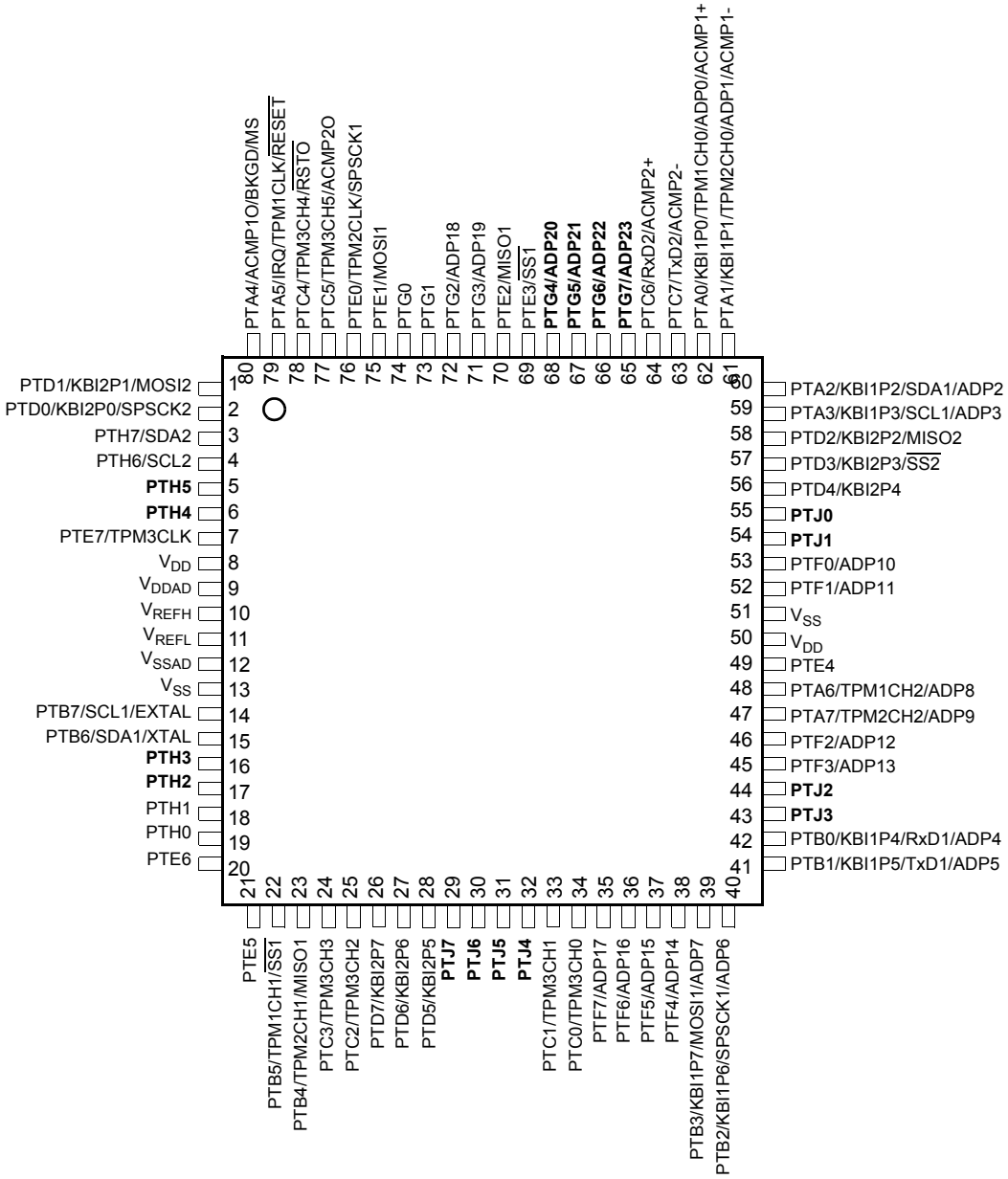


Figure 1. MC9S08QE128 Series Block Diagram

2 Pin Assignments

This section describes the pin assignments for the available packages. See Table 2 for pin availability by package pin-count.



Pins in **bold** are added from the next smaller package.

Figure 2. Pin Assignments in 80-Pin LQFP

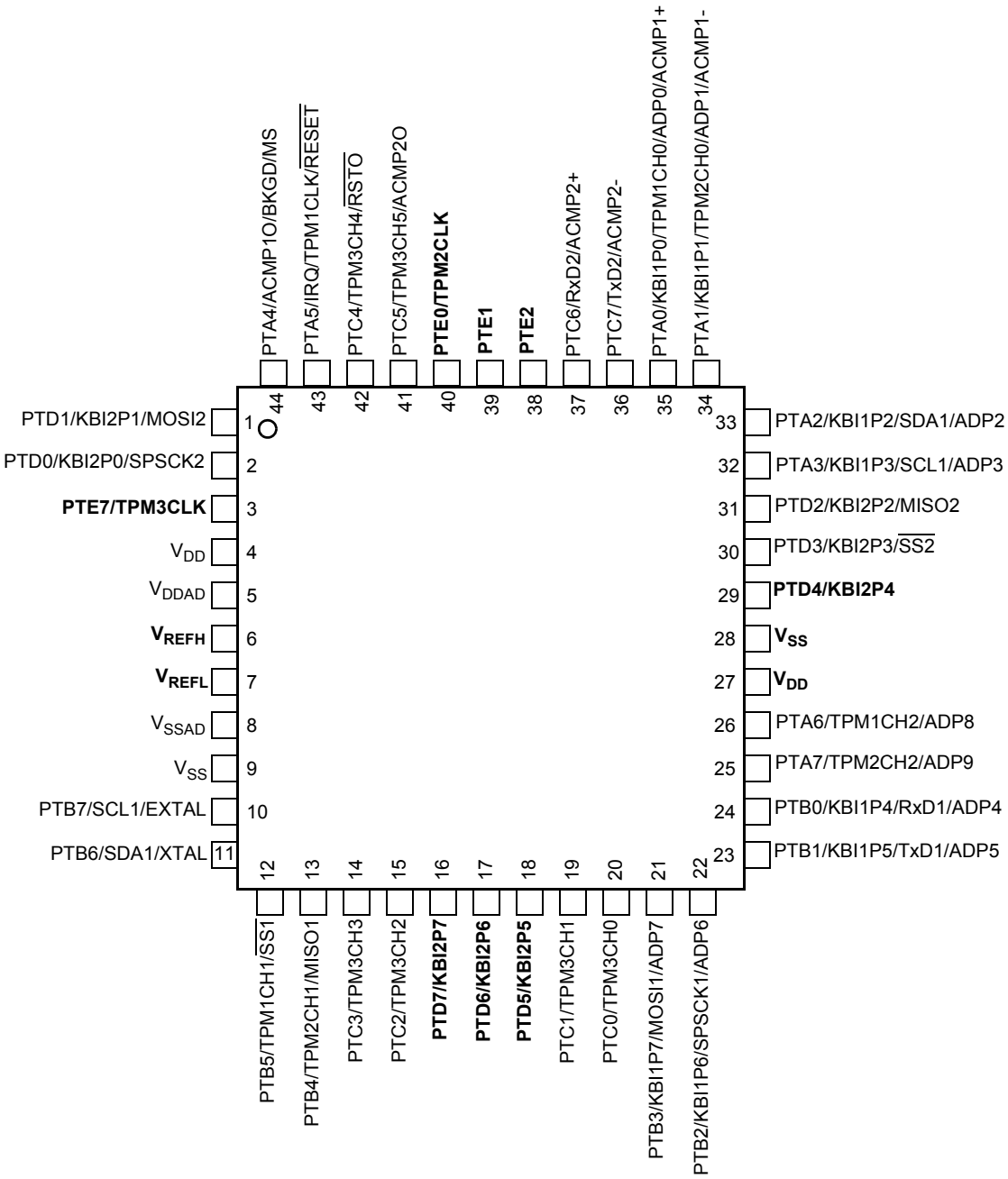


Figure 5. Pin Assignments in 44-Pin LQFP Package

Table 2. MC9S08QE128 Series Pin Assignment by Package and Pin Count (continued)

Pin Number					Lowest ← Priority → Highest				
80	**64**	**48**	**44**	**32**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt 3**	**Alt 4**
41	33	25	23	17	PTB1	KBI1P5	TxD1		ADP5
42	34	26	24	18	PTB0	KBI1P4	RxD1		ADP4
43	—	—	—	—	PTJ3				
44	—	—	—	—	PTJ2				
45	35	—	—	—	PTF3				ADP13
46	36	—	—	—	PTF2				ADP12
47	37	27	25	19	PTA7	TPM2CH2			ADP9
48	38	28	26	20	PTA6	TPM1CH2			ADP8
49	39	29	—	—	PTE4				
50	40	30	27	—					V_{DD}
51	41	31	28	—					V_{SS}
52	42	—	—	—	PTF1				ADP11
53	43	—	—	—	PTF0				ADP10
54	—	—	—	—	PTJ1				
55	—	—	—	—	PTJ0				
56	44	32	29	—	PTD4	KBI2P4			
57	45	33	30	21	PTD3	KBI2P3	$\overline{SS2}$		
58	46	34	31	22	PTD2	KBI2P2	MISO2		
59	47	35	32	23	PTA3	KBI1P3	SCL1		ADP3
60	48	36	33	24	PTA2	KBI1P2	SDA1		ADP2
61	49	37	34	25	PTA1	KBI1P1	TPM2CH0	ADP1	ACMP1-
62	50	38	35	26	PTA0	KBI1P0	TPM1CH0	ADP0	ACMP1+
63	51	39	36	27	PTC7	TxD2			ACMP2-
64	52	40	37	28	PTC6	RxD2			ACMP2+
65	—	—	—	—	PTG7				ADP23
66	—	—	—	—	PTG6				ADP22
67	—	—	—	—	PTG5				ADP21
68	—	—	—	—	PTG4				ADP20
69	53	41	—	—	PTE3	$\overline{SS1}$			
70	54	42	38	—	PTE2	MISO1			
71	55	—	—	—	PTG3				ADP19
72	56	—	—	—	PTG2				ADP18
73	57	—	—	—	PTG1				
74	58	—	—	—	PTG0				
75	59	43	39	—	PTE1	MOSI1			
76	60	44	40	—	PTE0	TPM2CLK	SPSCK1		
77	61	45	41	29	PTC5	TPM3CH5			ACMP2O
78	62	46	42	30	PTC4	TPM3CH4	$\overline{RSTO}$		
79	63	47	43	31	PTA5	IRQ	TPM1CLK	$\overline{RESET}$	
80	64	48	44	32	PTA4	ACMP1O	BKGD	MS	

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 6. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	3	
Machine	Series resistance	R1	0	Ω
	Storage capacitance	C	200	pF
	Number of pulses per pin	—	3	
Latch-up	Minimum input voltage limit		– 2.5	V
	Maximum input voltage limit		7.5	V

Table 7. ESD and Latch-Up Protection Characteristics

No.	Rating[1]	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	± 2000	—	V
2	Machine model (MM)	V_{MM}	± 200	—	V
3	Charge device model (CDM)	V_{CDM}	± 500	—	V
4	Latch-up current at T_A = 85°C	I_{LAT}	± 100	—	mA

1 Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

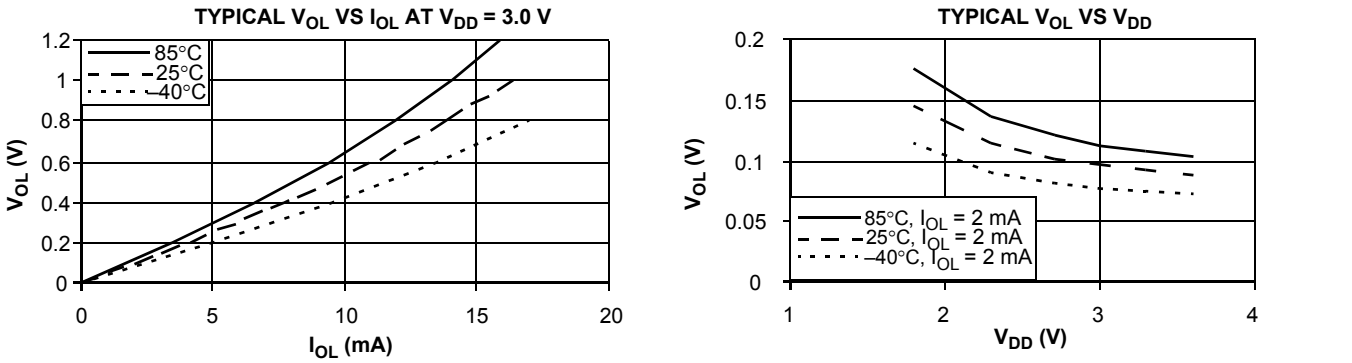


Figure 8. Typical Low-Side Driver (Sink) Characteristics — Low Drive (PTxDSn = 0)

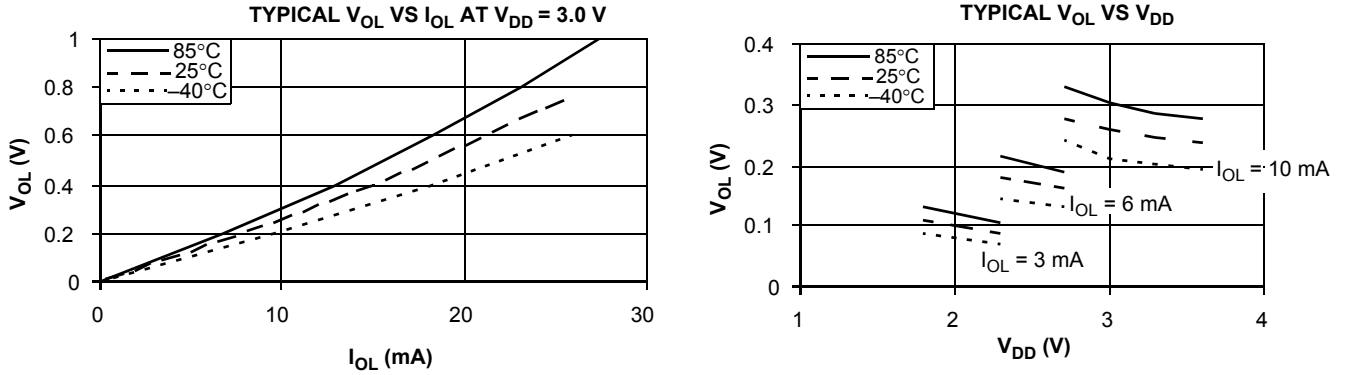


Figure 9. Typical Low-Side Driver (Sink) Characteristics — High Drive (PTxDSn = 1)

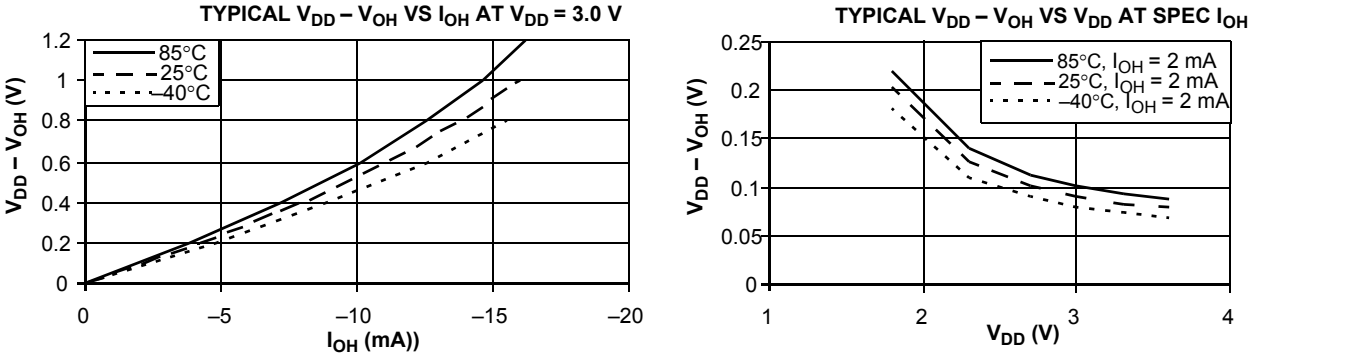


Figure 10. Typical High-Side (Source) Characteristics — Low Drive (PTxDSn = 0)

Table 9. Supply Current Characteristics (continued)

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)
6	P	Stop2 mode supply current	$S2I_{DD}$	n/a	3	0.35	0.6	μA	-40 to 25
	C					0.98	2.0		70
	P					2.5	7.5		85
	C				2	0.25	0.5		-40 to 25
	C					1.4	1.9		70
	C					1.91	6.5		85
7	P	Stop3 mode supply current No clocks active	$S3I_{DD}$	n/a	3	0.45	1.0	μA	-40 to 25
	C					1.99	4.2		70
	P					5.0	15.0		85
	C				2	0.35	0.7		-40 to 25
	C					2.9	3.9		70
	C					3.77	13.2		85

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

Table 10. Stop Mode Adders

Num	C	Parameter	Condition	Temperature (°C)				Units
				-40	25	70	85	
1	T	LPO		50	75	100	150	nA
2	T	ERREFSTEN	RANGE = HGO = 0	1000	1000	1100	1500	nA
3	T	IREFSTEN[1]		63	70	77	81	uA
4	T	RTC	does not include clock source current	50	75	100	150	nA
5	T	LVD[1]	LVDSE = 1	90	100	110	115	uA
6	T	ACMP[1]	not using the bandgap (BGBE = 0)	18	20	22	23	uA
7	T	ADC[1]	ADLPC = ADLSMP = 1 not using the bandgap (BGBE = 0)	95	106	114	120	uA

1 Not available in stop2 mode.

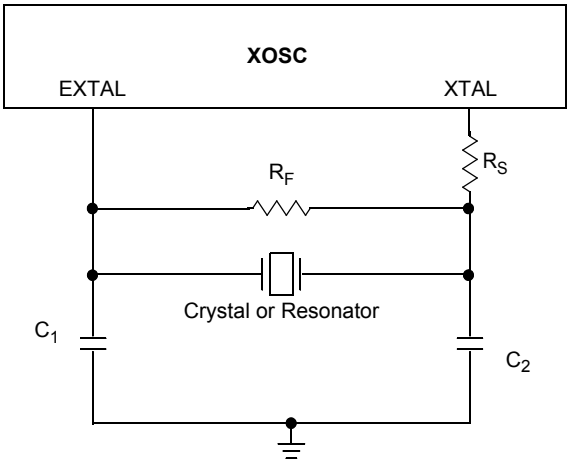


Figure 13. Typical Crystal or Resonator Circuit: High Range and Low Range/High Gain

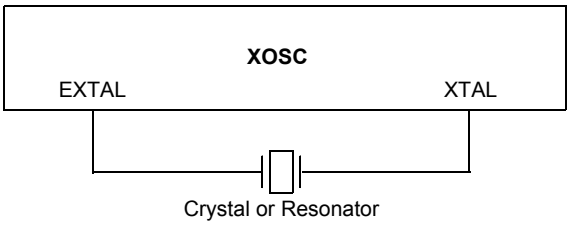


Figure 14. Typical Crystal or Resonator Circuit: Low Range/Low Gain

3.9 Internal Clock Source (ICS) Characteristics

Table 12. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient)

Num	C	Characteristic		Symbol	Min	Typ[1]	Max	Unit
1	P	Average internal reference frequency — factory trimmed at V_{DD} = 3.6 V and temperature = 25°C		f_{int_ft}	—	32.768	—	kHz
2	P	Internal reference frequency — user trimmed		f_{int_ut}	31.25	—	39.06	kHz
3	T	Internal reference start-up time		t_{IRST}	—	60	100	µs
4	P	DCO output frequency range — trimmed [2]	Low range (DRS=00)	f_{dco_u}	16	—	20	MHz
	P		Mid range (DRS=01)		32	—	40	
	P		High range (DRS=10)		48	—	60	
5	P	DCO output frequency [2] Reference = 32768 Hz and DMX32 = 1	Low range (DRS=00)	f_{dco_DMX32}	—	19.92	—	MHz
	P		Mid range (DRS=01)		—	39.85	—	
	P		High range (DRS=10)		—	59.77	—	
6	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco\_res\_t}$	—	± 0.1	± 0.2	$\%f_{dco}$
7	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco\_res\_t}$	—	± 0.2	± 0.4	$\%f_{dco}$

Table 12. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient) (continued)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
8	C	Total deviation of trimmed DCO output frequency over voltage and temperature	Δf_{dco_t}	—	+ 0.5 -1.0	± 2	$\%f_{dco}$
9	C	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0°C to 70 °C	Δf_{dco_t}	—	± 0.5	± 1	$\%f_{dco}$
10	C	FLL acquisition time [3]	$t_{Acquire}$	—	—	1	ms
11	C	Long term jitter of DCO output clock (averaged over 2-ms interval) [4]	C_{Jitter}	—	0.02	0.2	$\%f_{dco}$

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

2 The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

3 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

4 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

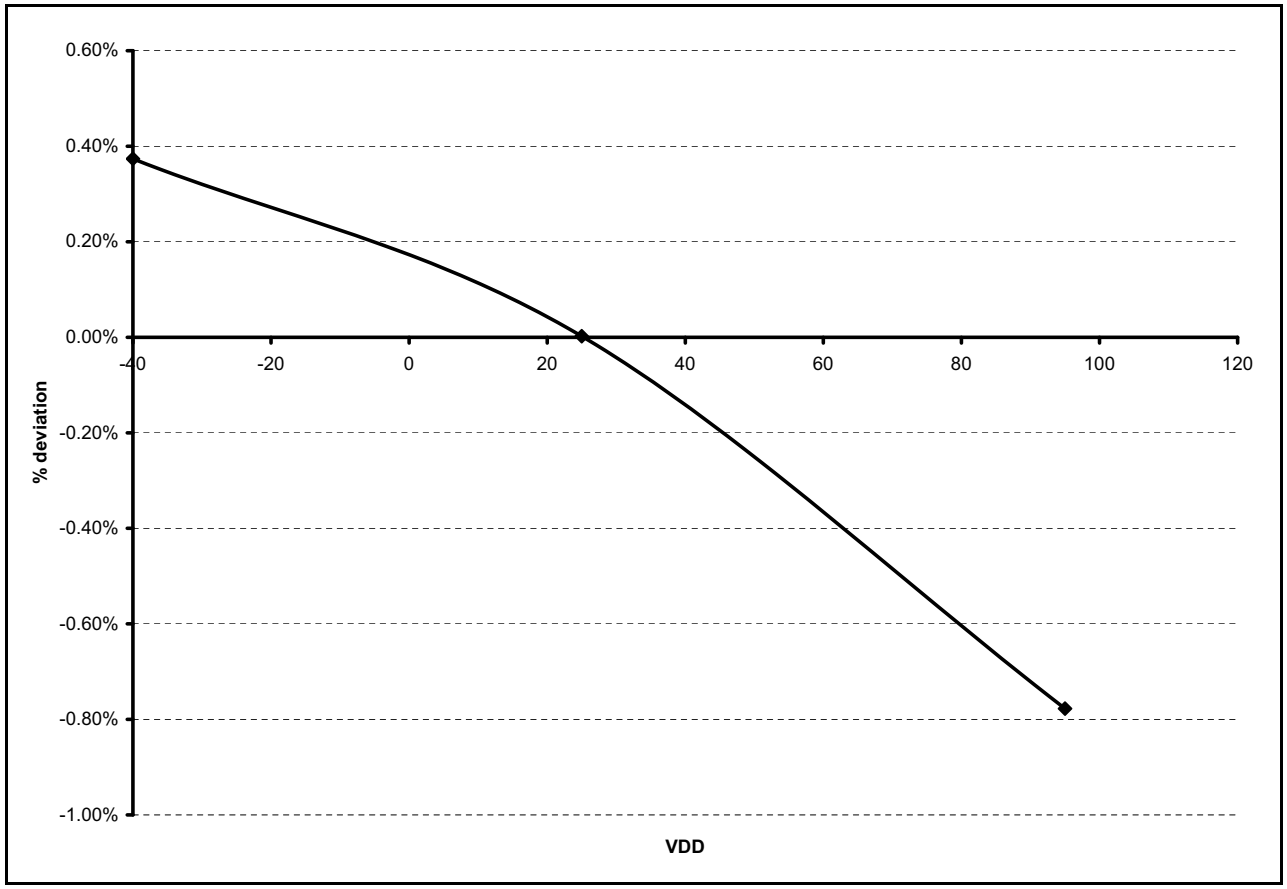


Figure 15. Deviation of DCO Output Across Temperature at V_{DD} = 3.0 V

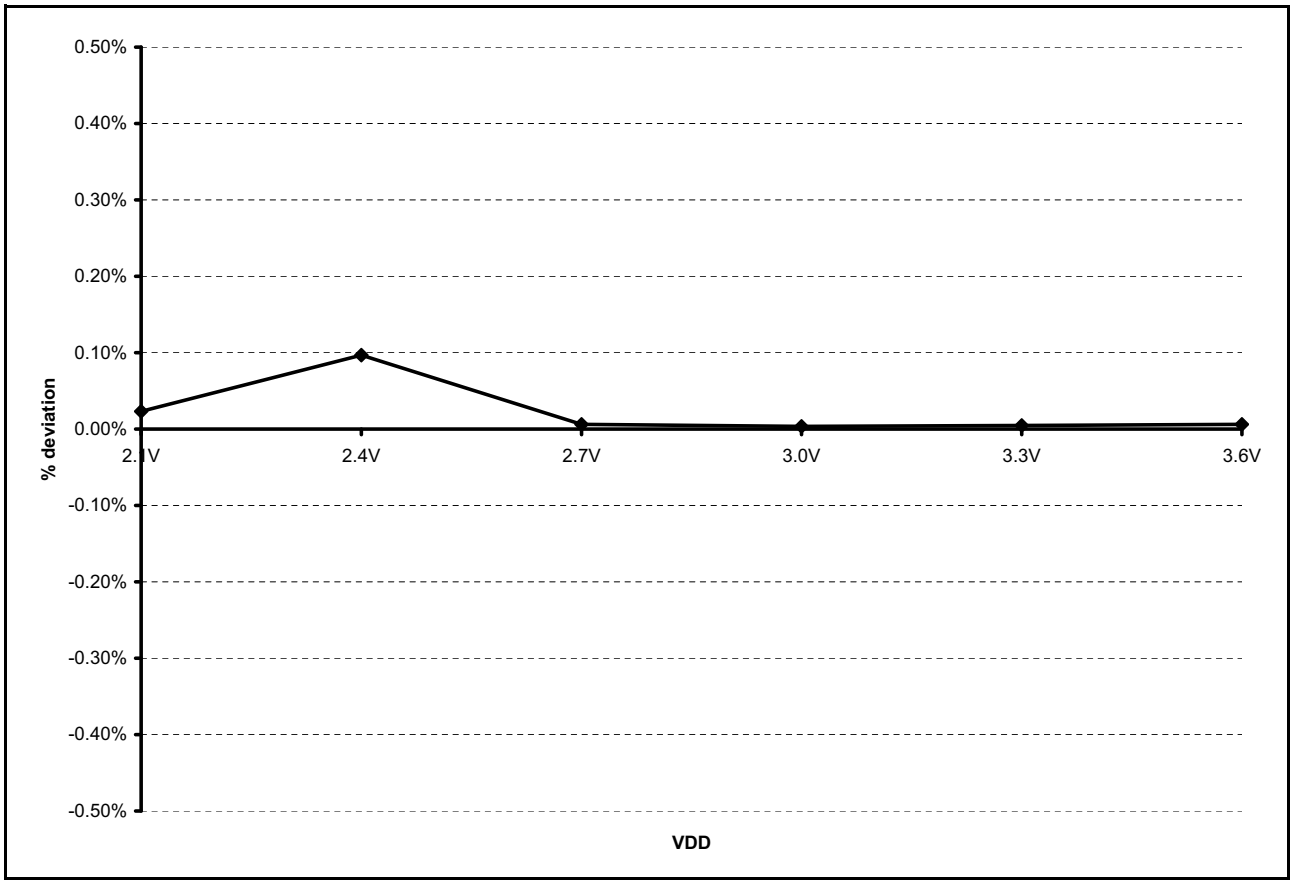


Figure 16. Deviation of DCO Output Across V_{DD} at 25°C

3.10 AC Characteristics

This section describes timing characteristics for each peripheral system.

3.10.1 Control Timing

Table 13. Control Timing

Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
1	D	Bus frequency (t_{cyc} = 1/f_{Bus}) $V_{DD} \geq 1.8V$ $V_{DD} > 2.1V$ $V_{DD} > 2.4V$	f_{Bus}	dc	— — —	10 20 25.165	MHz
2	D	Internal low power oscillator period	t_{LPO}	700	—	1300	µs
3	D	External reset pulse width[2]	t_{extrst}	100	—	—	ns
4	D	Reset low drive	t_{rstdrv}	34 x t_{cyc}	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes [3]	t_{MSH}	100	—	—	µs

3.10.2 TPM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 14. TPM Input Timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

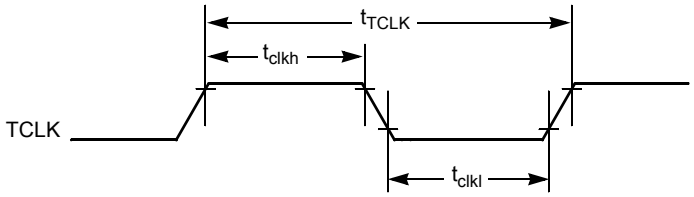


Figure 19. Timer External Clock

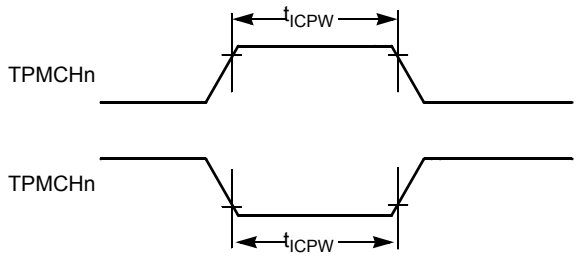
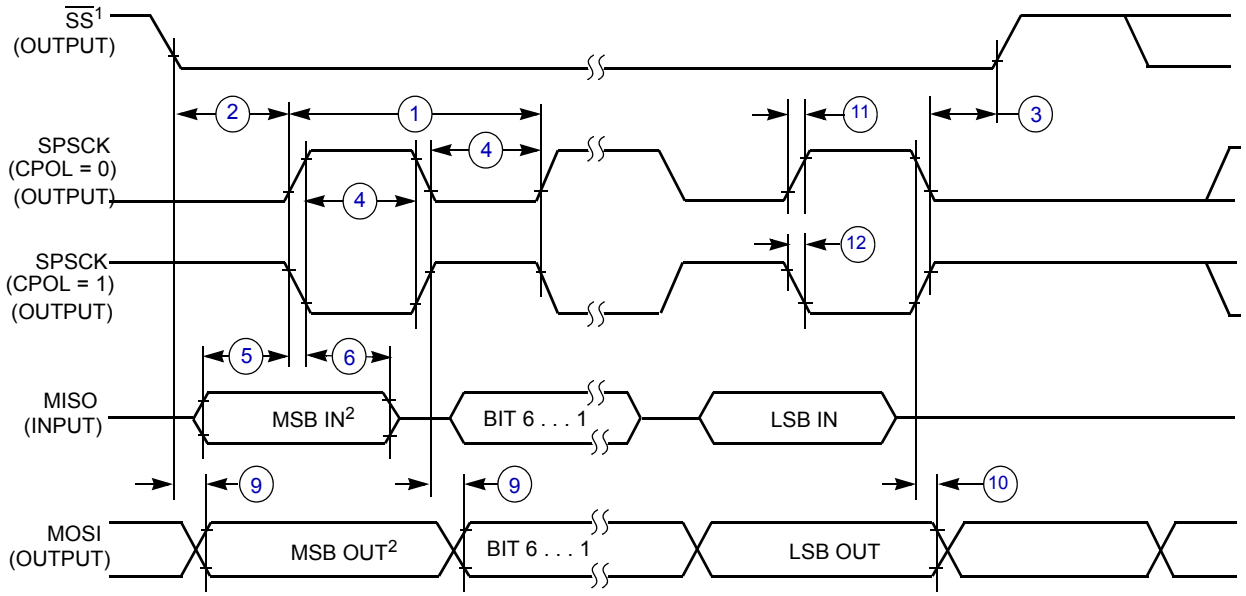
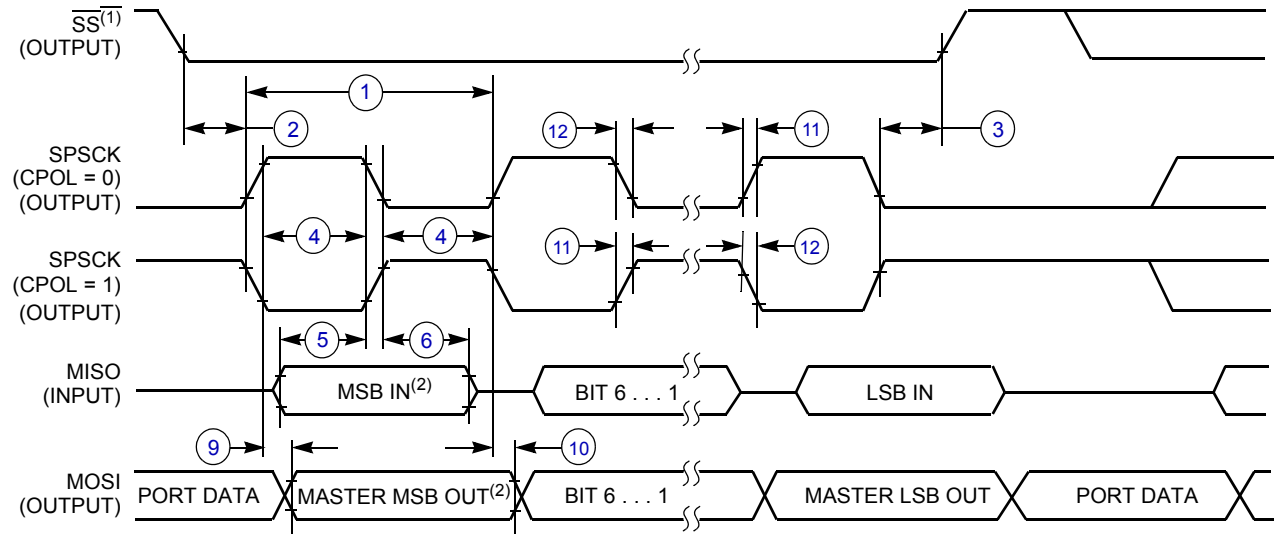


Figure 20. Timer Input Capture Pulse



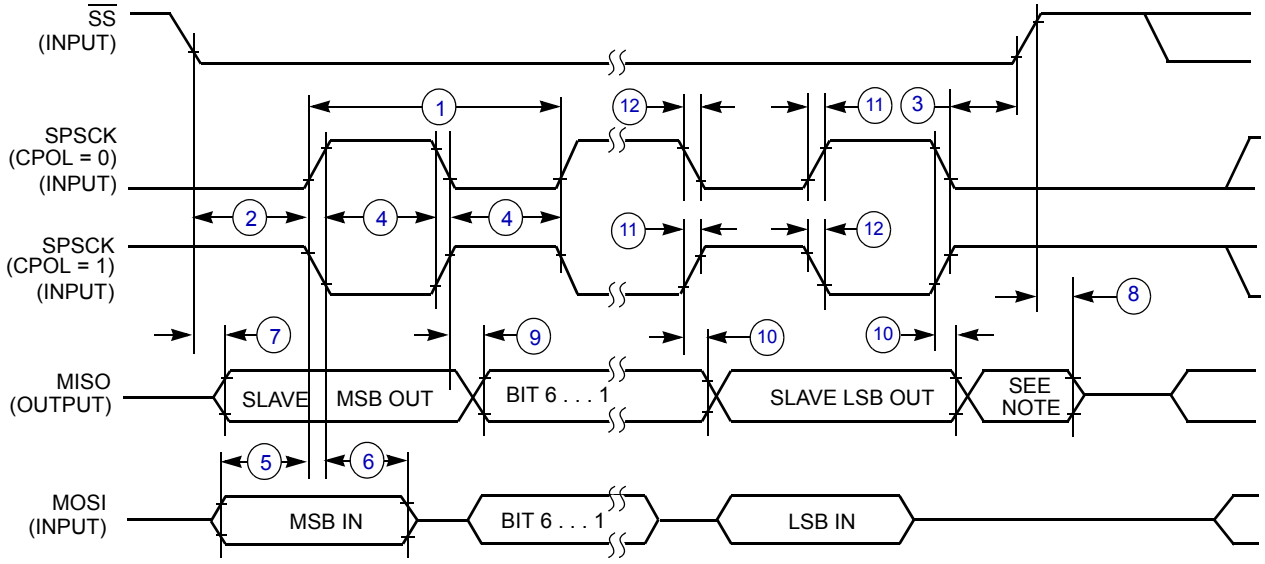
NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 21. SPI Master Timing (CPHA = 0)



NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

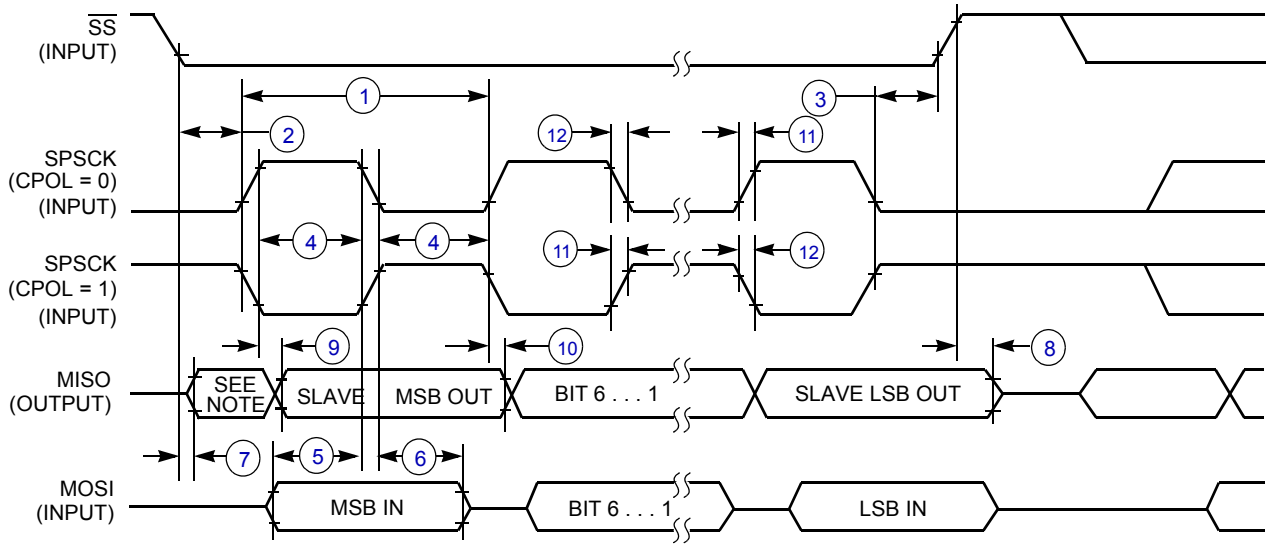
Figure 22. SPI Master Timing (CPHA =1)



NOTE:

1. Not defined but normally MSB of character just received

Figure 23. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined but normally LSB of character just received

Figure 24. SPI Slave Timing (CPHA = 1)

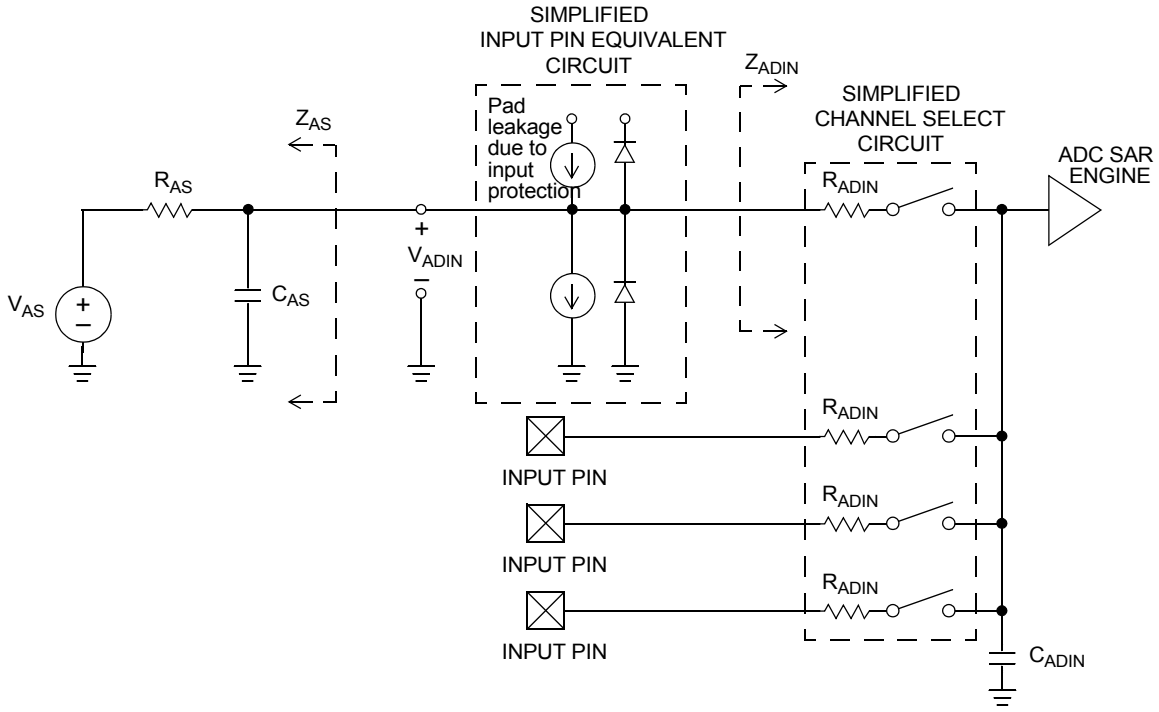


Figure 25. ADC Input Impedance Equivalency Diagram

Table 18. 12-bit ADC Characteristics (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD})

Characteristic	Conditions	C	Symb	Min	Typ[1]	Max	Unit	Comment
Supply Current ADLPC=1 ADLSMP=1 ADCO=1		T	I_{DDAD}	—	120	—	μA	
Supply Current ADLPC=1 ADLSMP=0 ADCO=1		T	I_{DDAD}	—	202	—	μA	
Supply Current ADLPC=0 ADLSMP=1 ADCO=1		T	I_{DDAD}	—	288	—	μA	
Supply Current ADLPC=0 ADLSMP=0 ADCO=1		D	I_{DDAD}	—	0.532	1	mA	
Supply Current	Stop, Reset, Module Off	P	I_{DDAD}	—	0.007	0.8	μA	
ADC Asynchronous Clock Source	High Speed (ADLPC=0)	P	f_{ADACK}	2	3.3	5	MHz	$t_{ADACK} = 1/f_{ADACK}$
	Low Power (ADLPC=1)	P		1.25	2	3.3		

Table 18. 12-bit ADC Characteristics (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD}) (continued)

Characteristic	Conditions	C	Symb	Min	Typ[1]	Max	Unit	Comment
Conversion Time (Including sample time)	Short Sample (ADLSMP=0)	P	t_{ADC}	—	20	—	ADCK cycles	See the ADC chapter in the MC9S08*QE128 Reference Manual* for conversion time variances
	Long Sample (ADLSMP=1)	C		—	40	—		
Sample Time	Short Sample (ADLSMP=0)	P	t_{ADS}	—	3.5	—	ADCK cycles	
	Long Sample (ADLSMP=1)	C		—	23.5	—		
Total Unadjusted Error	12 bit mode	T	E_{TUE}	—	±3.0	—	LSB[2]	Includes Quantization
	10 bit mode	P		—	±1	±2.5		
	8 bit mode	T		—	±0.5	±1.0		
Differential Non-Linearity	12 bit mode	T	DNL	—	±1.75	—	LSB[2]	
	10 bit mode[3]	P		—	±0.5	±1.0		
	8 bit mode[3]	T		—	±0.3	±0.5		
Integral Non-Linearity	12 bit mode	T	INL	—	±1.5	—	LSB[2]	
	10 bit mode	T		—	±0.5	±1.0		
	8 bit mode	T		—	±0.3	±0.5		
Zero-Scale Error	12 bit mode	T	E_{ZS}	—	±1.5	—	LSB[2]	V_{ADIN} = V_{SSAD}
	10 bit mode	P		—	±0.5	±1.5		
	8 bit mode	T		—	±0.5	±0.5		
Full-Scale Error	12 bit mode	T	E_{FS}	—	±1.0	—	LSB[2]	V_{ADIN} = V_{DDAD}
	10 bit mode	P		—	±0.5	±1		
	8 bit mode	T		—	±0.5	±0.5		
Quantization Error	12 bit mode	D	E_Q	—	-1 to 0	—	LSB[2]	
	10 bit mode			—	—	±0.5		
	8 bit mode			—	—	±0.5		
Input Leakage Error	12 bit mode	D	E_{IL}	—	±2	—	LSB[2]	Pad leakage[4] * R_{AS}
	10 bit mode			—	±0.2	±4		
	8 bit mode			—	±0.1	±1.2		
Temp Sensor Slope	-40°C to 25°C	D	m	—	1.646	—	mV/°C	
	25°C to 85°C			—	1.769	—		
Temp Sensor Voltage	25°C	D	V_{TEMP25}	—	701.2	—	mV	

1 Typical values assume V_{DDAD} = 3.0V, Temp = 25°C, f_{ADCK}=1.0MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 1 LSB = $(V_{REFH} - V_{REFL})/2^N$

3 Monotonicity and No-Missing-Codes guaranteed in 10 bit and 8 bit modes

4 Based on input pad leakage current. Refer to pad electricals.

4 Ordering Information

This section contains ordering information for MC9S08QE128, MC9S08QE96, and MC9S08QE64 devices.

Table 20. Ordering Information

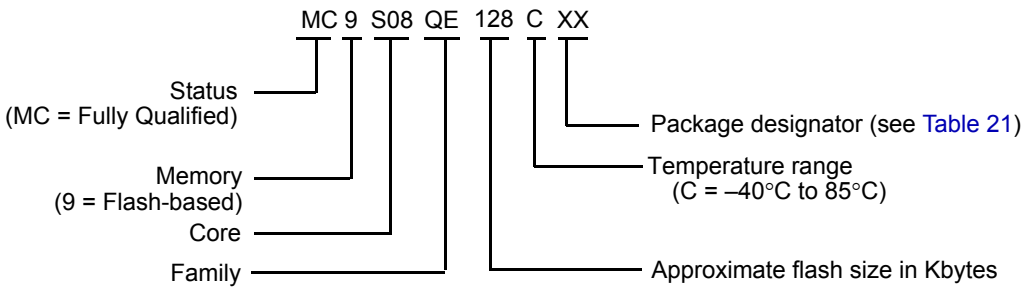
Freescale Part Number[1]	Memory		Temperature range (°C)	Package[2]
	Flash	RAM		
MC9S08QE128CLK	128K	8K	-40 to +85	80 LQFP
MC9S08QE128CLH			-40 to +85	64 LQFP
MC9S08QE128CFT			-40 to +85	48 QFN
MC9S08QE128CLD			-40 to +85	44 LQFP
MC9S08QE96CLK	96K	6K	-40 to +85	80 LQFP
MC9S08QE96CLH			-40 to +85	64 LQFP
MC9S08QE96CFT			-40 to +85	48 QFN
MC9S08QE96CLD			-40 to +85	44 QFP
MC9S08QE64CLH	64K	4K	-40 to +85	64 LQFP
MC9S08QE64CFT			-40 to +85	48 QFN
MC9S08QE64CLD			-40 to +85	44 QFP
MC9S08QE64CLC			-40 to +85	32 LQFP

1 See the reference manual, *MC9S08QE128RM*, for a complete description of modules included on each device.

2 See Table 21 for package information.

4.1 Device Numbering System

Example of the device numbering system:

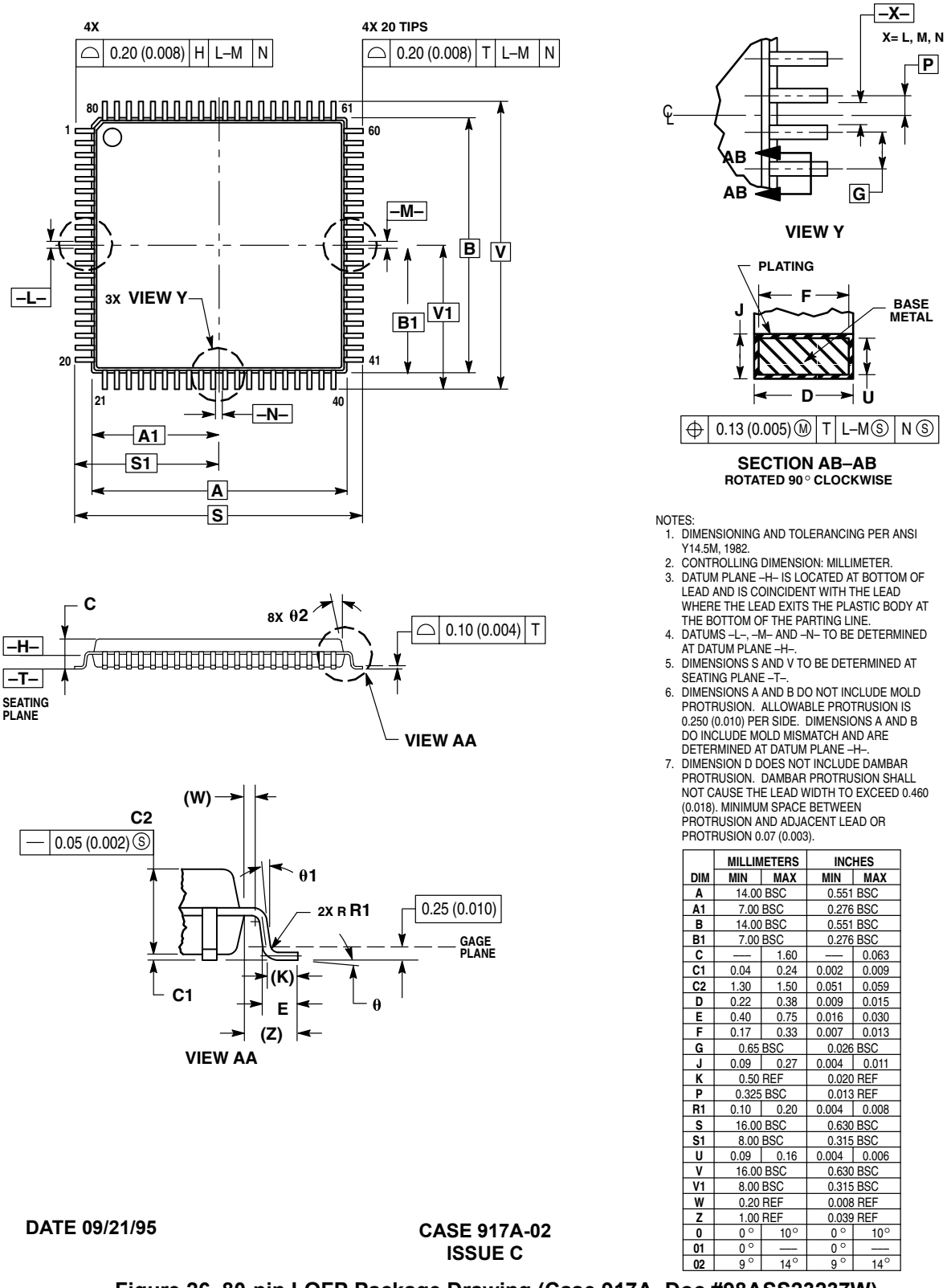


5 Package Information

The below table details the various packages available.

Table 21. Package Descriptions

Pin Count	Package Type	Abbreviation	Designator	Case No.	Document No.
80	Low Quad Flat Package	LQFP	LK	917A	98ASS23237W
64	Low Quad Flat Package	LQFP	LH	840F	98ASS23234W
48	Quad Flat No-Leads	QFN	FT	1314	98ARH99048A
44	Low Quad Flat Package	LQFP	LD	824D	98ASS23225W
32	Low Quad Flat Package	LQFP	LC	873A	98ASH70029A



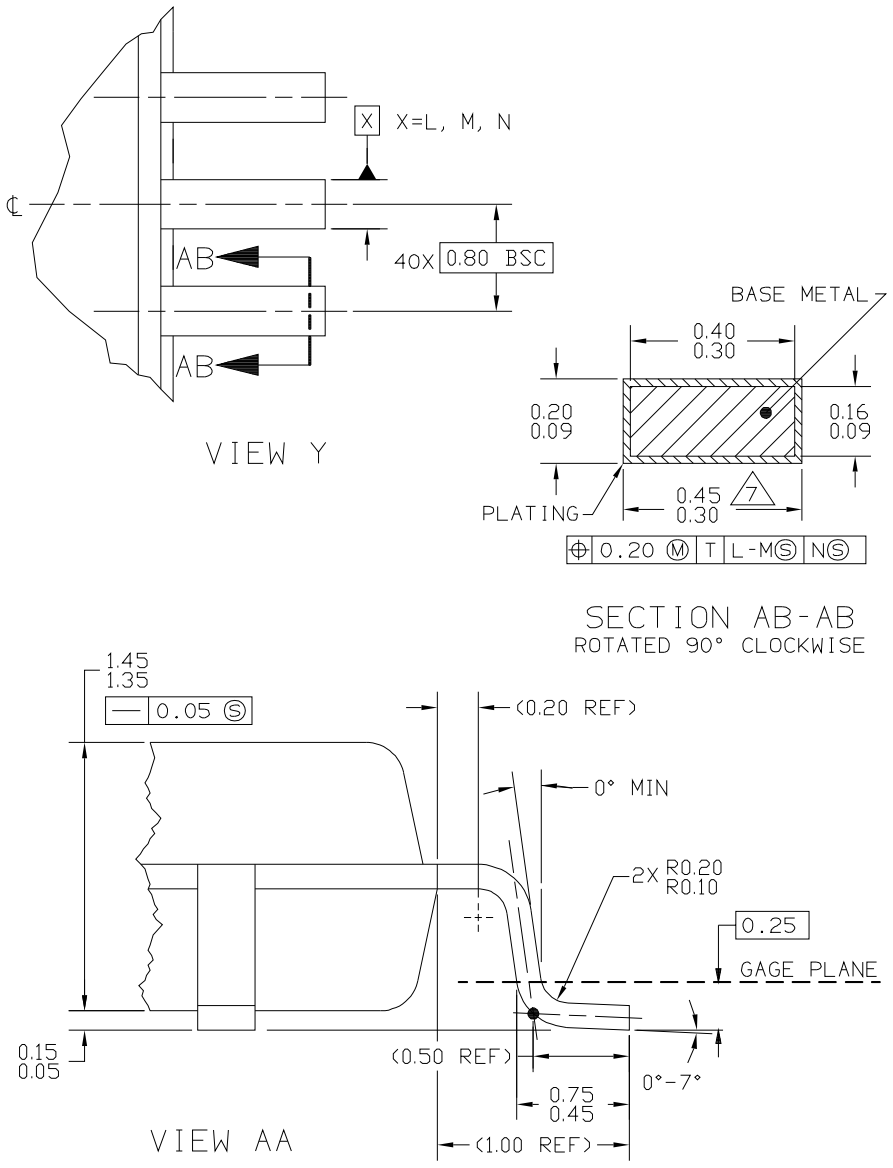
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DATUM PLANE –H– IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DATUMS –L–, –M– AND –N– TO BE DETERMINED AT DATUM PLANE –H–.
5. DIMENSIONS S AND V TO BE DETERMINED AT SEATING PLANE –T–.
6. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.250 (0.010) PER SIDE. DIMENSIONS A AND B DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE –H–.
7. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.460 (0.018). MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION 0.07 (0.003).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	14.00 BSC		0.551 BSC	
A1	7.00 BSC		0.276 BSC	
B	14.00 BSC		0.551 BSC	
B1	7.00 BSC		0.276 BSC	
C	—	1.60	—	0.063
C1	0.04	0.24	0.002	0.009
C2	1.30	1.50	0.051	0.059
D	0.22	0.38	0.009	0.015
E	0.40	0.75	0.016	0.030
F	0.17	0.33	0.007	0.013
G	0.65 BSC		0.026 BSC	
J	0.09	0.27	0.004	0.011
K	0.50 REF		0.020 REF	
P	0.325 BSC		0.013 REF	
R1	0.10	0.20	0.004	0.008
S	16.00 BSC		0.630 BSC	
S1	8.00 BSC		0.315 BSC	
U	0.09	0.16	0.004	0.006
V	16.00 BSC		0.630 BSC	
V1	8.00 BSC		0.315 BSC	
W	0.20 REF		0.008 REF	
Z	1.00 REF		0.039 REF	
θ	0°	10°	0°	10°
θ1	0°	—	0°	—
θ2	9°	14°	9°	14°

DATE 09/21/95

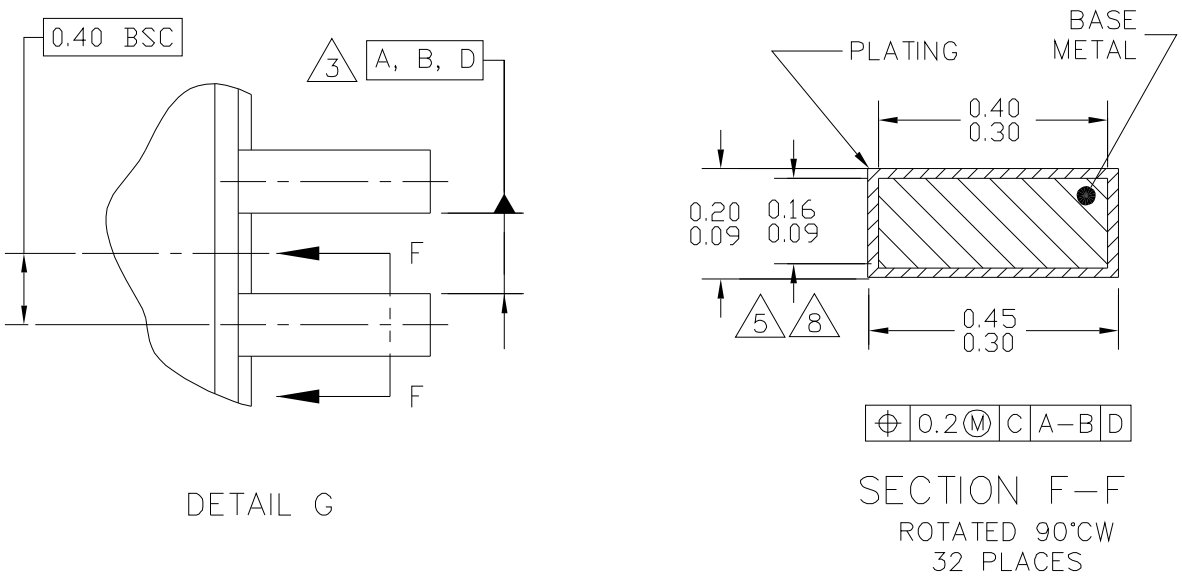
CASE 917A-02
ISSUE C

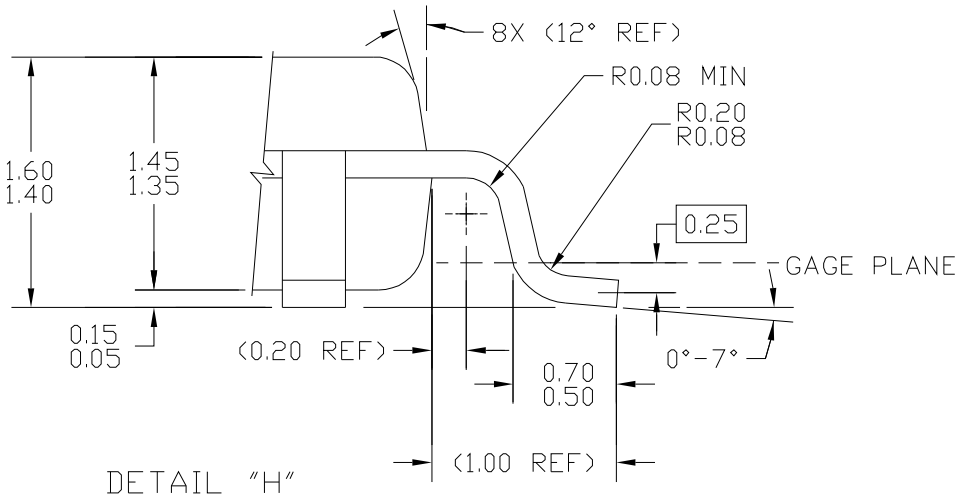
Figure 26. 80-pin LQFP Package Drawing (Case 917A, Doc #98ASS23237W)



© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
TITLE: 44 LD LQFP, 10 X 10 PKG, 0.8 PITCH, 1.4 THICK	DOCUMENT NO: 98ASS23225W	REV: D
	CASE NUMBER: 824D-02	26 FEB 2007
	STANDARD: JEDEC MS-026 BCB	

Figure 34. 44-pin LQFP Package Drawing (Case 824D, Doc #98ASS23225W), Sheet 2 of 3





© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	DOCUMENT NO: 98ASH70029A	REV: D
	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

Figure 37. 32-pin LQFP Package Drawing (Case 873A, Doc #98ASH70029A), Sheet 2 of 3